

## Description

The IRF7316PBF uses advanced trench technology and design to provide excellent RDS(ON) with low gat e charge. It can be used in a wide variety of applications.

## **General Features**

 $V_{DS} = -30V, I_D = -5.3A$ 

 $R_{DS(ON)} < 42m$  @ V<sub>GS</sub>=-10V

RDS(ON) < 85m @ VGS=-4.5V

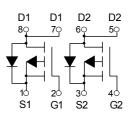
# Application

#### PWM application

Load switch







#### **Dual P-Channel MOSFET**

### Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IRF7316PBF	SOP-8	HXY MOSFET	3000

## Absolute Maximum Ratings (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Symbol	Parameter	Limit	Unit
Vds	Drain-Source Voltage	-30	V
Vgs	Gate-Source Voltage	±20	V
D	Drain Current-Continuous	-5.3	A
Ырм	Drain Current-Pulsed (Note 1)	-20	A
PD	Maximum Power Dissipation	2.6	W
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	49	°C <b>/W</b>



#### Electrical Characteristics (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250µA	-30	-33	-	V
Zero Gate Voltage Drain Current	loss	V <sub>DS</sub> =-24V,V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	Igss	GSS VGS=±20V,VDS=0V		-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250µA	-1	-1.6	-3	V
			-	35	42	mR
Drain-Source On-State Resistance	RDS(ON)	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.2A	-	70	85	mR
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =-15V,I <sub>D</sub> =-4.5A	4	7	-	S
Dynamic Characteristics (Note4)		I				
Input Capacitance	Clss		-	540	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V,	-	150	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	75	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	td(on)		-	8	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =-15V, ID=-1A,	-	14	-	nS
Turn-Off Delay Time	td(off)	V <sub>GS</sub> =-10V,R <sub>GEN</sub> =6	-	18	-	nS
Turn-Off Fall Time	tr		-	10	-	nS
Total Gate Charge	Qg		-	12	-	nC
Gate-Source Charge	Qgs	V <sub>DS</sub> =-15V,I <sub>D</sub> =-5.3A,V <sub>GS</sub> =- 10V	-	2.4	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3.2	-	nC
Drain-Source Diode Characteristics	1	1		1		
Diode Forward Voltage (Note 3)	Vsd	V <sub>GS</sub> =0V,I <sub>S</sub> =-5.3A	-	-	-1.2	V

### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

**2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.

**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production



t<sub>d(off)</sub>

**INVERTED** 

**PULSE WIDTH** 

Figure 2:Switching Waveforms

90%

10%

90%

50%

10%

509

t<sub>d(on)</sub>

V<sub>OUT</sub>

V<sub>IN</sub>

10%

# **Typical Electrical and Thermal Characteristics**

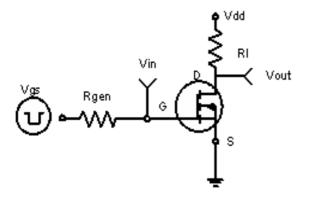
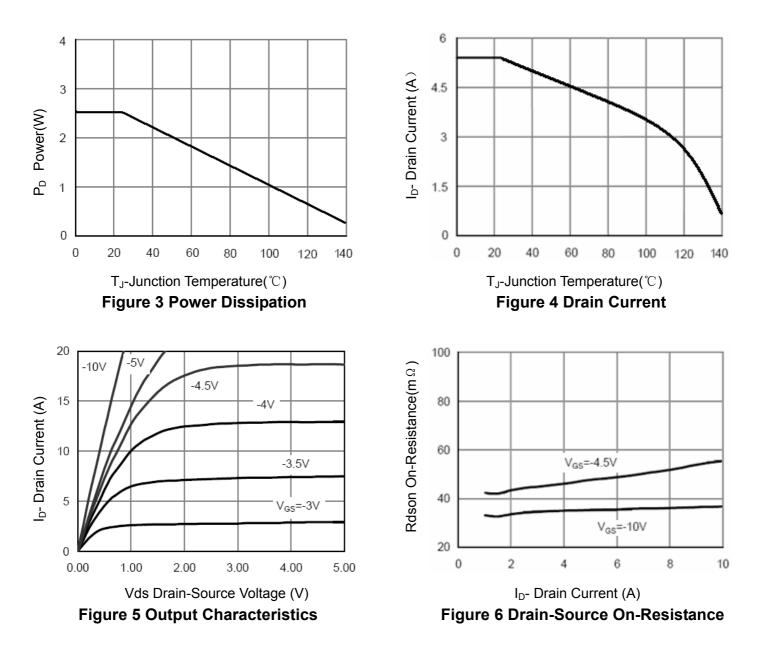
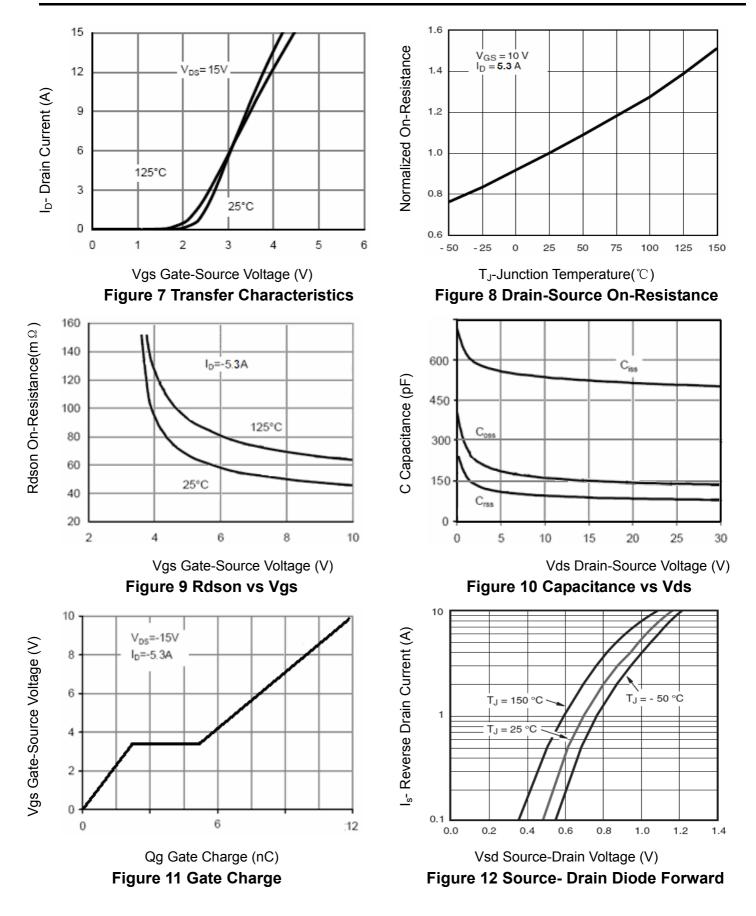


Figure 1:Switching Test Circuit

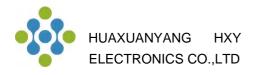




## IRF7316PBF Dual P-Channel Enhancement Mode MOSFET







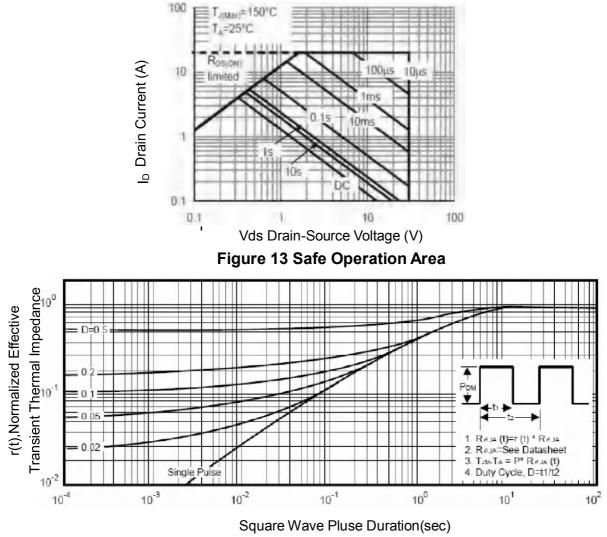
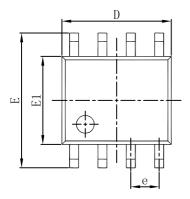
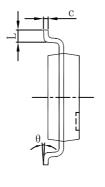


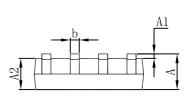
Figure 14 Normalized Maximum Transient Thermal Impedance



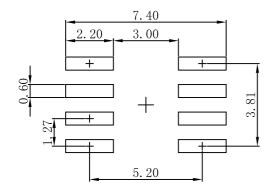
# **SOP-8 Package Outline Dimensions**







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
с	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0.197	
e	1.270 (BSC)		0.050 (BSC)		
E	5.800	6.200	0.228	0.244	
E1	3.800	4.000	0.150	0.157	
L	0.400	1.270	0.016	0.050	
θ	0 °	8°	0 °	8°	



Note: 1.Controlling dimension: in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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